

GigaMOS™ TrenchT2
HiperFET™
Power MOSFET

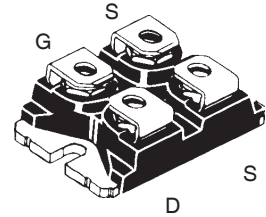
IXFN320N17T2

$$\begin{aligned} V_{DSS} &= 170V \\ I_{D25} &= 260A \\ R_{DS(on)} &\leq 5.2m\Omega \\ t_{rr} &\leq 150ns \end{aligned}$$

N-Channel Enhancement Mode
 Avalanche Rated
 Fast Intrinsic Diode



miniBLOC, SOT-227
 E153432



G = Gate D = Drain
 S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|--|-----------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 175°C | 170 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 175°C , $R_{GS} = 1M\Omega$ | 170 | V |
| V_{GSS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ (Chip Capability) | 260 | A |
| $I_{L(RMS)}$ | External Lead Current Limit | 200 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM} | 800 | A |
| I_A | $T_C = 25^\circ\text{C}$ | 100 | A |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 5 | J |
| dV/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 175^\circ\text{C}$ | 20 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 1070 | W |
| T_J | | -55 ... +175 | $^\circ\text{C}$ |
| T_{JM} | | 175 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +175 | $^\circ\text{C}$ |
| T_L | 1.6mm (0.062 in.) from Case for 10s | 300 | $^\circ\text{C}$ |
| T_{SOLD} | Plastic Body for 10s | 260 | $^\circ\text{C}$ |
| V_{ISOL} | 50/60 Hz, RMS $t = 1$ minute | 2500 | V~ |
| | $I_{ISOL} \leq 1\text{mA}$ $t = 1$ second | 3000 | V~ |
| M_d | Mounting Torque | 1.5/13 | Nm/lb.in. |
| | Terminal Connection Torque | 1.3/11.5 | Nm/lb.in. |
| Weight | | 30 | g |

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500 V~
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Synchronous Rectification
- DC-DC Converters
- Battery Chargers
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 3\text{mA}$ | 170 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 8\text{mA}$ | 2.5 | | 5.0 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 150^\circ\text{C}$ | | | 50 μA 5 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 60A$, Note 1 | | | 5.2 m Ω |

| Symbol | Test Conditions | Characteristic Values | | |
|--------------|--|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 10V, I_D = 60A$, Note 1 | 120 | 190 | S |
| C_{iss} | $V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$ | | 45 | nF |
| C_{oss} | | | 2890 | pF |
| C_{rss} | | | 410 | pF |
| R_{Gi} | Gate Input Resistance | | 1.96 | Ω |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 100A$ $R_G = 1\Omega$ (External) | | 46 | ns |
| t_r | | | 170 | ns |
| $t_{d(off)}$ | | | 115 | ns |
| t_f | | | 230 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 160A$ | | 640 | nC |
| Q_{gs} | | | 185 | nC |
| Q_{gd} | | | 175 | nC |
| R_{thJC} | | | 0.14 | $^{\circ}C/W$ |
| R_{thCS} | | 0.05 | | $^{\circ}C/W$ |

Source-Drain Diode

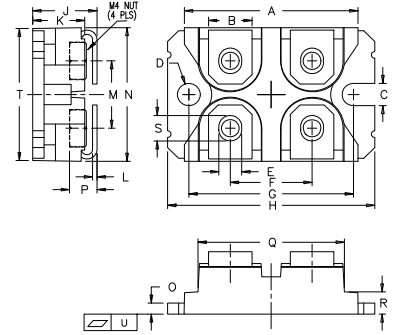
| Symbol | Test Conditions | Characteristic Values | | |
|----------|---|-----------------------|------|---------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0V$ | | | 320 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 1280 A |
| V_{SD} | $I_F = 100A, V_{GS} = 0V$, Note 1 | | | 1.25 V |
| t_{rr} | $I_F = 160A, -di/dt = 100A/\mu s$ $V_R = 60V, V_{GS} = 0V$ | | | 150 ns |
| Q_{RM} | | | 0.53 | μC |
| I_{RM} | | | 9.00 | A |

Note 1. Pulse test, $t \leq 300\mu s$; duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

SOT-227B (IXFN) Outline



(M4 screws (4x) supplied)

| SYM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 1.240 | 1.255 | 31.50 | 31.88 |
| B | .307 | .323 | 7.80 | 8.20 |
| C | .161 | .169 | 4.09 | 4.29 |
| D | .161 | .169 | 4.09 | 4.29 |
| E | .161 | .169 | 4.09 | 4.29 |
| F | .587 | .595 | 14.91 | 15.11 |
| G | 1.186 | 1.193 | 30.12 | 30.30 |
| H | 1.496 | 1.505 | 38.00 | 38.23 |
| J | .460 | .481 | 11.68 | 12.22 |
| K | .351 | .378 | 8.92 | 9.60 |
| L | .030 | .033 | 0.76 | 0.84 |
| M | .496 | .506 | 12.60 | 12.85 |
| N | .990 | 1.001 | 25.15 | 25.42 |
| O | .078 | .084 | 1.98 | 2.13 |
| P | .195 | .235 | 4.95 | 5.97 |
| Q | 1.045 | 1.059 | 26.54 | 26.90 |
| R | .155 | .174 | 3.94 | 4.42 |
| S | .186 | .191 | 4.72 | 4.85 |
| T | .968 | .987 | 24.59 | 25.07 |
| U | -.002 | .004 | -0.05 | 0.1 |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics
@ $T_J = 25^\circ\text{C}$

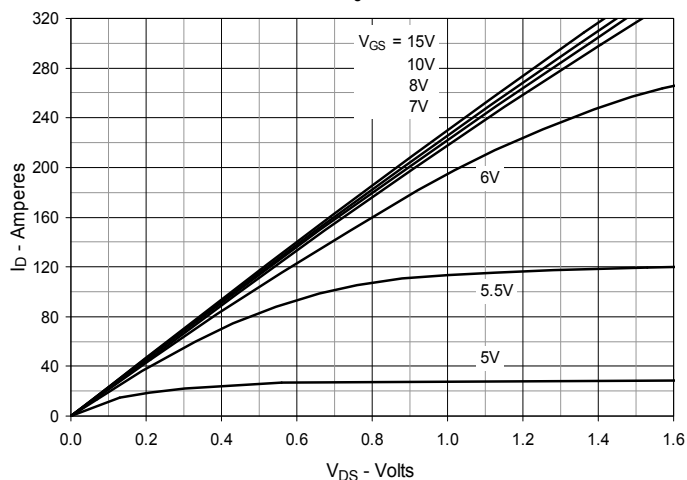


Fig. 2. Extended Output Characteristics
@ $T_J = 25^\circ\text{C}$

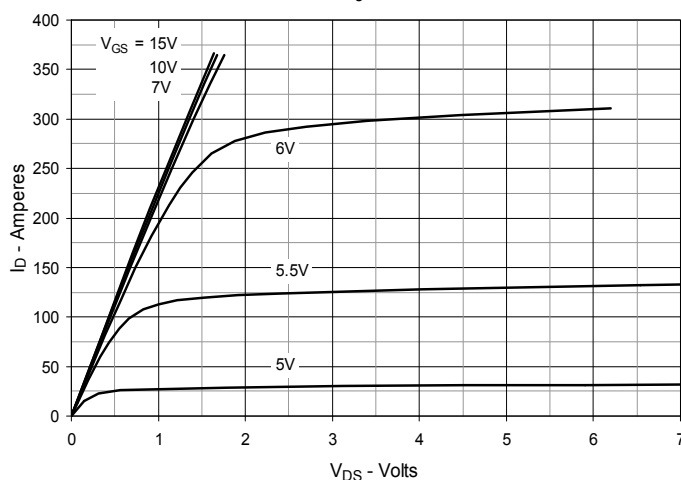


Fig. 3. Output Characteristics
@ $T_J = 150^\circ\text{C}$

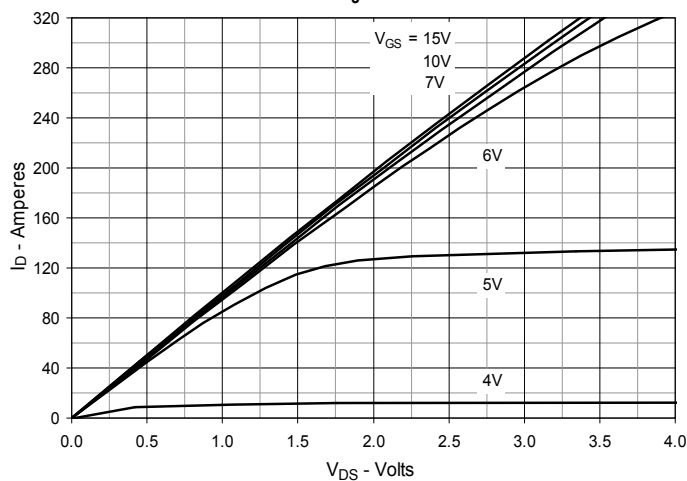


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 160\text{A}$ Value vs. Junction Temperature

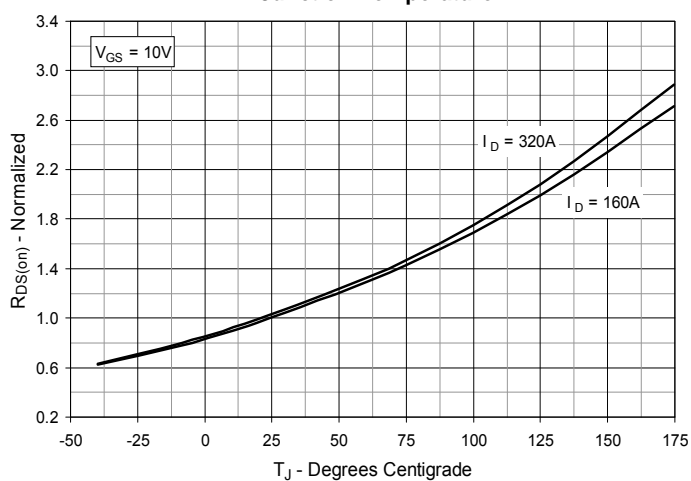


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 160\text{A}$ Value vs. Drain Current

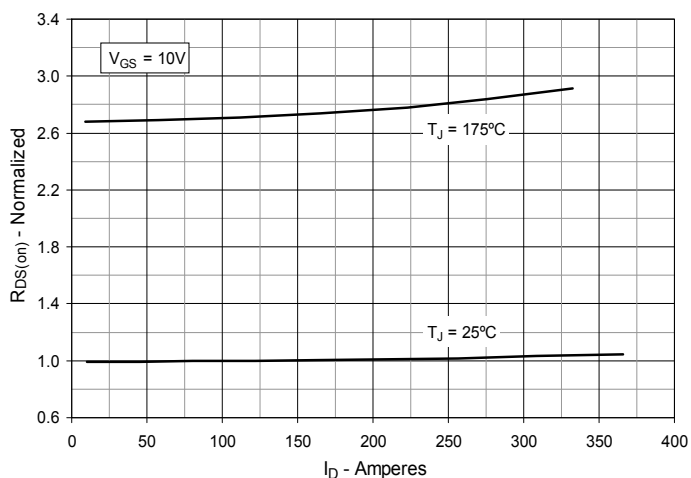


Fig. 6. Drain Current vs. Case Temperature

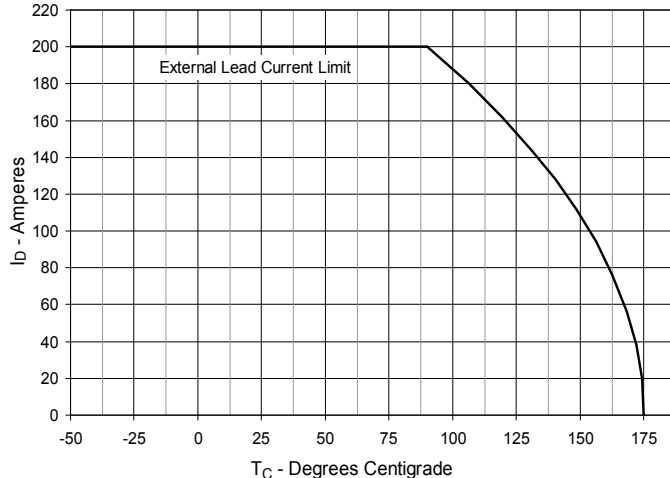


Fig. 7. Input Admittance

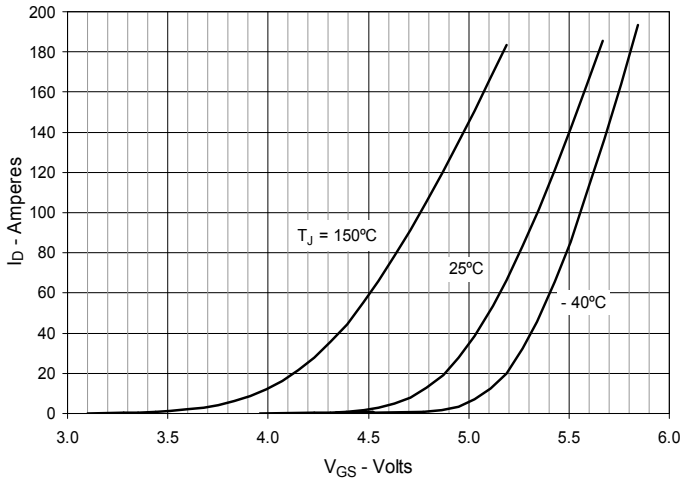


Fig. 8. Transconductance

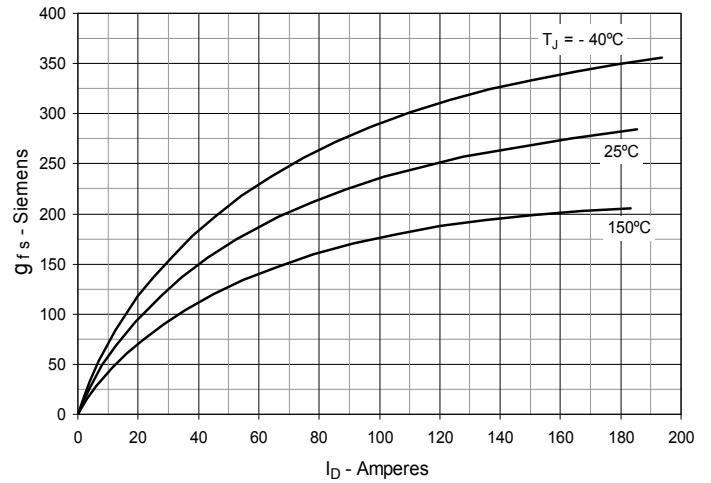


Fig. 9. Forward Voltage Drop of Intrinsic Diode

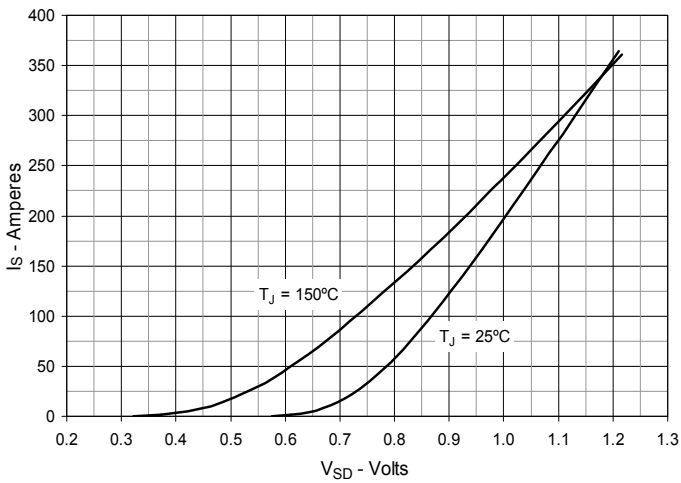


Fig. 10. Gate Charge

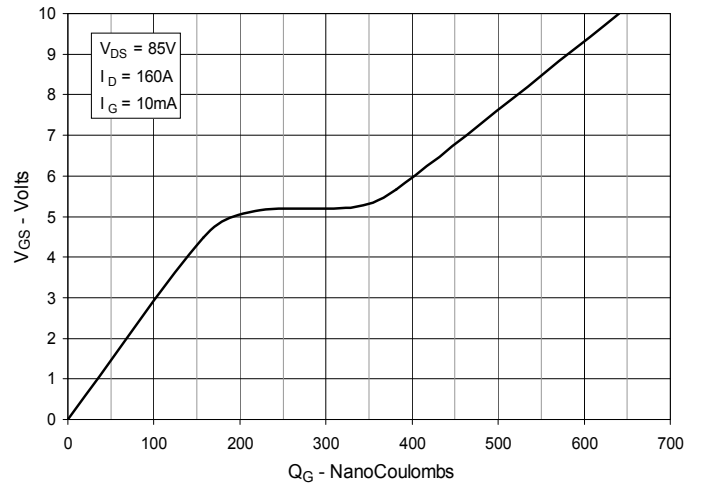


Fig. 11. Capacitance

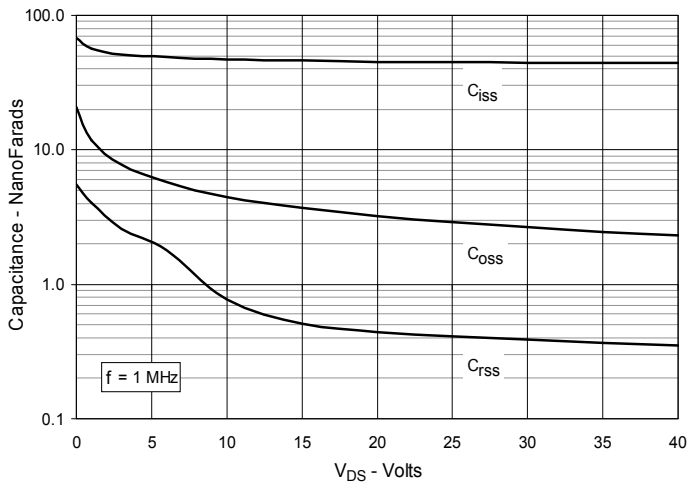


Fig. 12. Forward-Bias Safe Operating Area

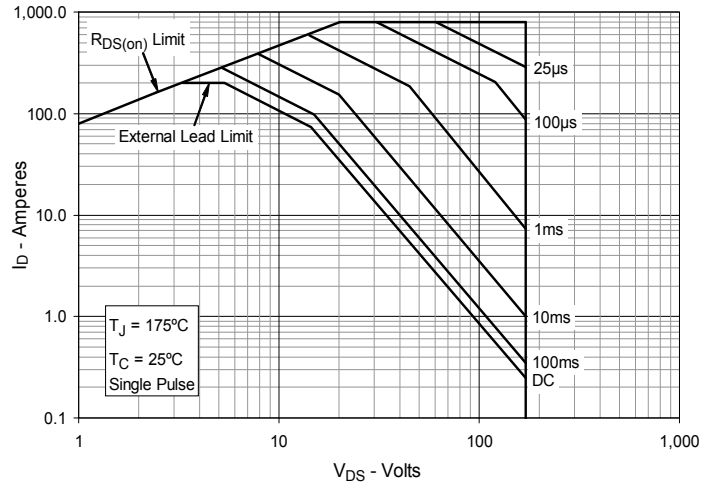


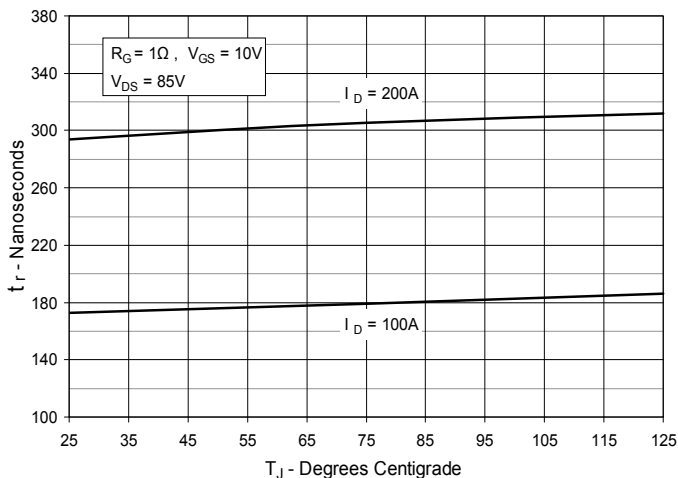
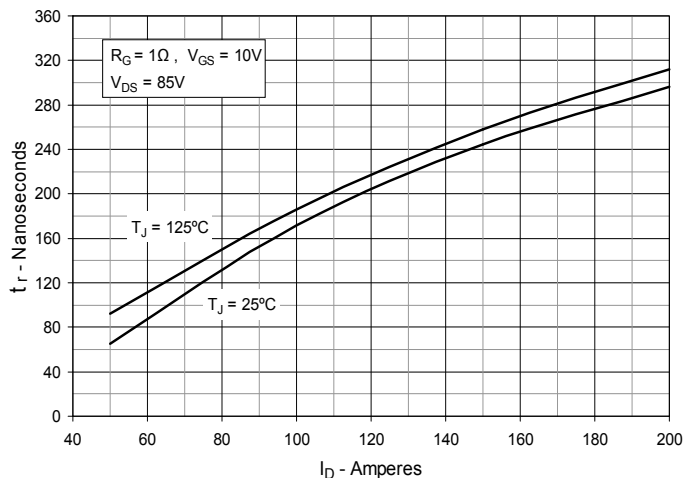
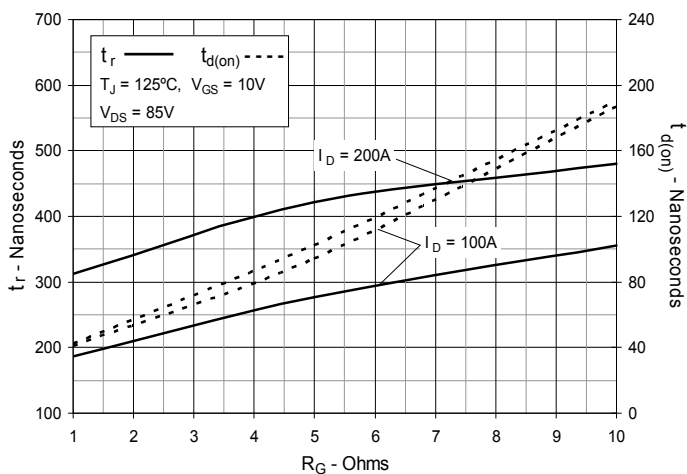
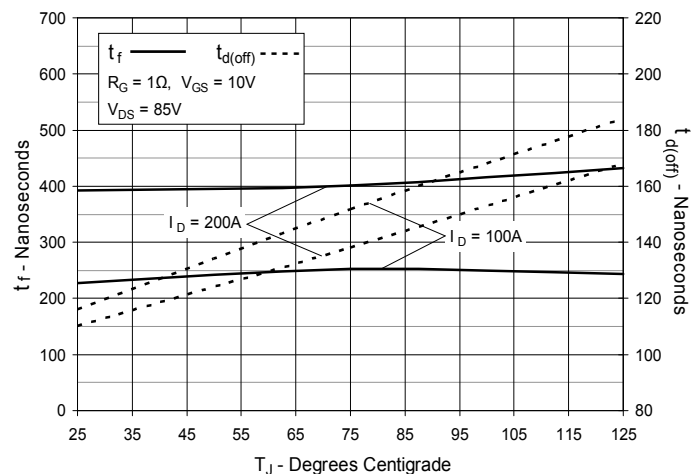
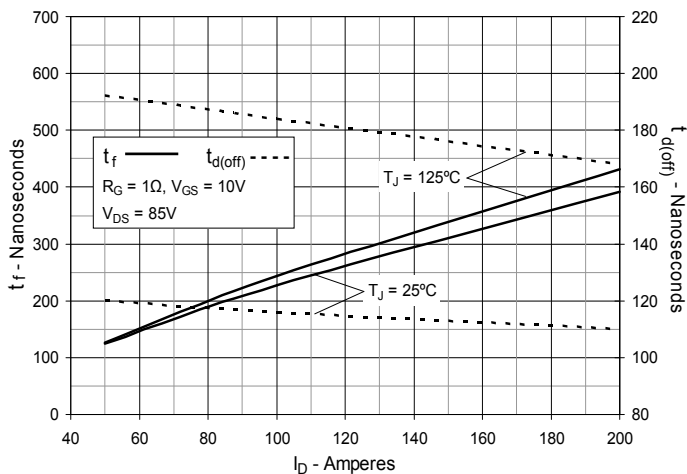
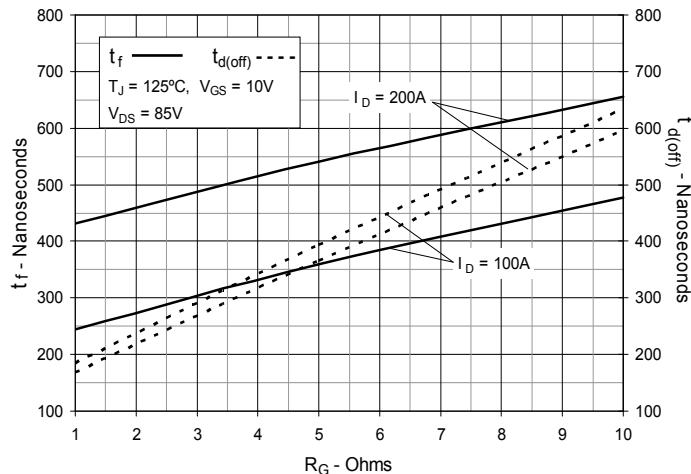
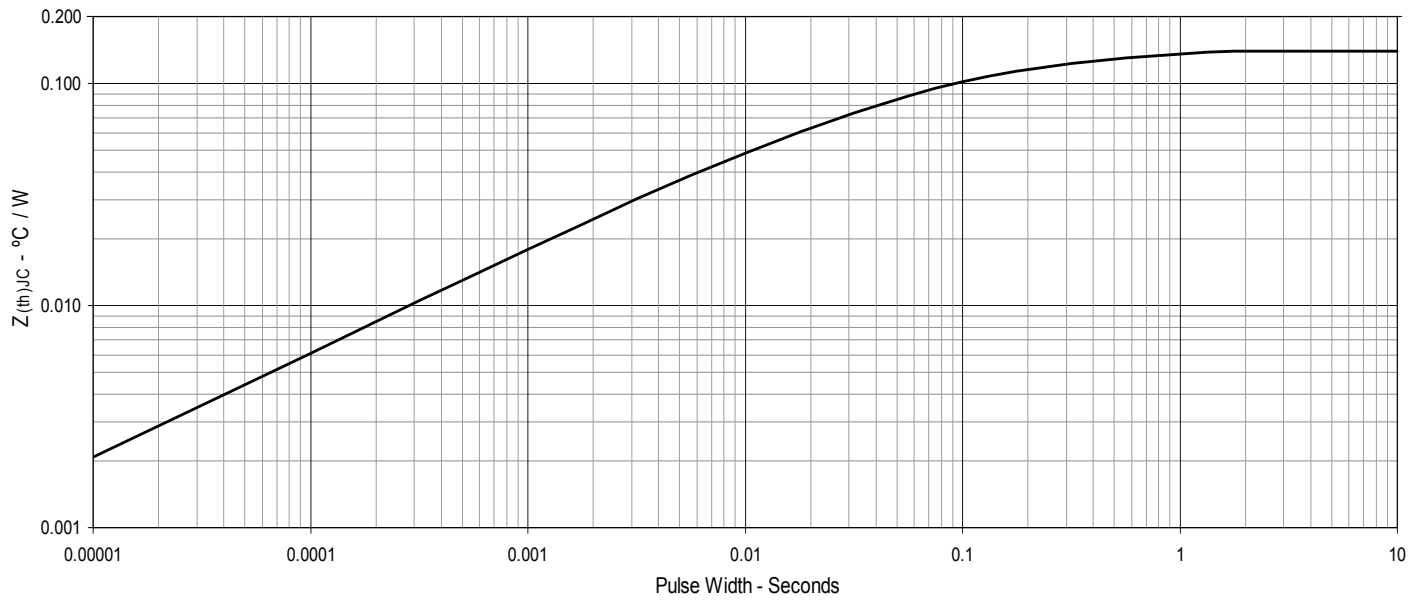
Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance


Fig. 19. Maximum Transient Thermal Impedance





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